

WHAT IS CLAIMED IS:

1. A semiconductor device, comprising:
  - a first conductive layer;
  - a first ball formed on said first conductive layer;
  - a second conductive layer arranged spaced apart from said first conductive layer;
  - 5 a second ball formed on said second conductive layer; and
  - a bonding wire connecting said first and second balls; wherein said second ball is formed by mechanically deforming said bonding wire.
2. The semiconductor device according to claim 1, wherein said second ball is formed by bending said bonding wire on said second conductive layer.
3. The semiconductor device according to claim 1, wherein said second ball is formed by making said bonding wire curved on said second conductive layer.
4. The semiconductor device according to claim 1, wherein said first conductive layer includes an inner lead; and said second conductive layer includes a bonding pad.
5. The semiconductor device according to claim 1, comprising:
  - a base;
  - a semiconductor element formed on said base with a die pad interposed;
  - 5 a sealing resin sealing said semiconductor element; and
  - an external terminal formed on a rear surface of said base; wherein said first conductive layer includes a land formed on said base, and said second conductive layer includes a bonding pad formed on said semiconductor element.

6. The semiconductor device according to claim 1, comprising:  
a base;  
first and second semiconductor elements mounted on said base with  
a die pad interposed;  
5 a sealing resin sealing said first and second semiconductor elements;  
and  
an external terminal formed on a rear surface of said base; wherein  
said first conductive layer includes a first bonding pad formed on  
said first semiconductor element, and  
10 said second conductive layer includes a second bonding pad formed  
on said second semiconductor element.

7. A method of manufacturing a semiconductor device, comprising:  
a first bonding step of joining a first ball formed at a tip end of a  
bonding wire to a first conductive layer;  
5 after said first bonding step, joining said bonding wire to a second  
conductive layer;  
mechanically deforming said bonding wire on said second conductive  
layer, with said bonding wire joined to the second conductive layer; and  
a second bonding step of joining the deformed portion of said  
bonding wire to said second conductive layer.

8. The method of manufacturing a semiconductor device according  
to claim 7, wherein  
said step of mechanically deforming said bonding wire includes the  
step of bending said bonding wire on said second conductive layer.

9. The method of manufacturing a semiconductor device according  
to claim 7, wherein  
said step of mechanically deforming said bonding wire includes the  
step of making said bonding wire curved on said second conductive layer.

10. The method of manufacturing a semiconductor device according to claim 7, wherein

    said bonding wire is held by a bonding tool; and

    said step of mechanically deforming said bonding wire includes the  
5   step of mechanically deforming said bonding wire on said second conductive layer by moving said bonding tool with said bonding wire being joined to said second conductive layer.